



## Type SF071-xx25 Fast Stud Mounted Thyristor

Distributed amplified gate for high di/dt and low switching losses

Maximum mean on-state current					<b><math>I_{TAV}</math></b>	<b>250 A</b>			
Maximum repetitive peak off-state and reverse voltage					<b><math>U_{DRM}</math></b>	<b>300 ÷ 1100 V</b>			
Turn-off time					<b><math>U_{RRM}</math></b>	<b>12,5; 16; 20 <math>\mu</math>s</b>			
					<b><math>t_q</math></b>				
$U_{DRM}, U_{RRM}, V$	300	400	500	600	700	800	900	1000	1100
Voltage code - <b>XX</b>	3	4	5	6	7	8	9	10	11
$T_{vj}, ^\circ C$	- 60 ÷ 125								

### MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	SF071-xx25	Conditions
$I_{TAV}$	Mean on-state current	A	250	$T_c=90^\circ C$ , 180° half-sine wave, 50 Hz
$I_{TRMS}$	RMS on-state current	A	392	$T_c=90^\circ C$
$I_{TSM}$	Surge on-state current	KA	7,0	$T_{vj}=125^\circ C$ $U_R=0$ $t_p=10$ ms
$(di_T/dt)_{cr}$	Critical rate of rise of on-state current : non - repetitive repetitive	A/ $\mu$ s	1600 800	$T_{vj}=125^\circ C$ ; $U_D=0,67 U_{DRM}$ , Gate pulse : 10V,5 $\Omega$ , 1 $\mu$ s rise time, 10 $\mu$ s
$U_{RGM}$	Peak reverse gate voltage	V	5	
$T_{stg}$	Storage temperature	$^\circ C$	-60 ÷ 125	
$T_{vj}$	Junction temperature	$^\circ C$	-60 ÷ 125	

### CHARACTERISTICS

Symbols and parameters		Units	SF071-xx25	Conditions
$U_{TM}$	Peak on-state voltage	V	2,1	$T_{vj}=25^\circ C$ , $I_{TM}=3,14 I_{TAV}$
$U_{T(To)}$	Threshold voltage	V	1,3	$T_{vj}=125^\circ C$
$R_T$	On-state slope resistance	m $\Omega$	0,7	$T_{vj}=125^\circ C$
$I_{DRM}$	Repetitive peak off-state and reverse current	mA	50	$T_{vj}=125^\circ C$ , $U_D = U_{DRM}$
$I_{RRM}$		50	50	$U_R = U_{RRM}$
$I_H$	Holding current	A	0,3	$T_{vj}=25^\circ C$ , $U_D=12V$ , Gate open

UGT	Gate trigger direct voltage	V	2,5	Tvj=25°C, UD=12V
IGT	Gate trigger direct current	A	0,3	
UGD	Gate non-trigger direct voltage	V	0,25	Tvj=125°C, UD = 0,67 UDRM
tgD	Delay time	μs	1,6	Tvj=25°C, UD=300V ITM = 250 A
tgt	Turn-on time	μs	2,5	Gate pulse : 10V, 5Ω, 1 μs rise time, 10μs
tq	Turn-off time	μs	12,5÷20 16÷25	Tvj=125°C, ITM=250 A dir/dt=10 A/μs, UR=100V UD = 0,67 UDRM duD/dt=50 V/μs duD/dt=200 V/μs
(duD/dt)crit	Critical rate of rise of off-state voltage	V/μs	500 1000	Tvj=125°C, UD = 0,67 UDRM Gate open
Rthjc	Thermal resistance junction to case	°C/W	0,075	Direct current

Tightening torque : 40 ÷ 60 Nm  
Weight : 480 grams

